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**SI2309DS**

60V P-Channel Power MOSFET

[www.sot23.com.tw](http://www.sot23.com.tw)

### General Features

- $V_{DS} = -60V, I_D = -1.6A$
- $R_{DS(ON)} < 200m\Omega @ V_{GS} = -10V$
- $R_{DS(ON)} < 240m\Omega @ V_{GS} = -4.5V$

### Application

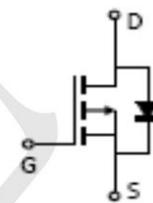
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

### Package and Pin Configuration

SOT-23



Circuit diagram



### Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	-1.6	A
Pulsed Drain Current <sup>(Note 1)</sup>	$I_{DM}$	-8	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

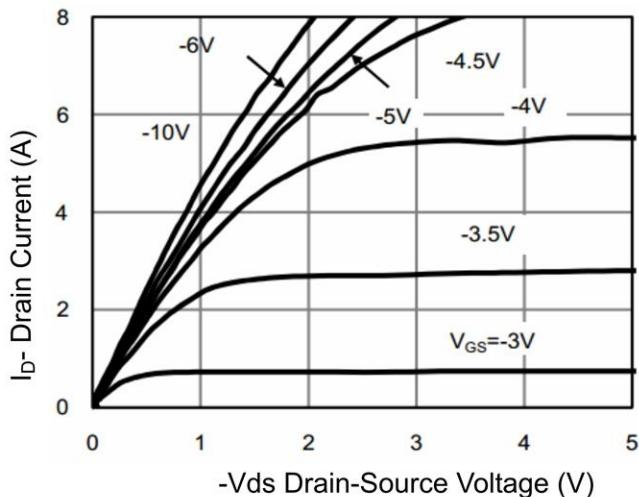
Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	83.3	°C/W
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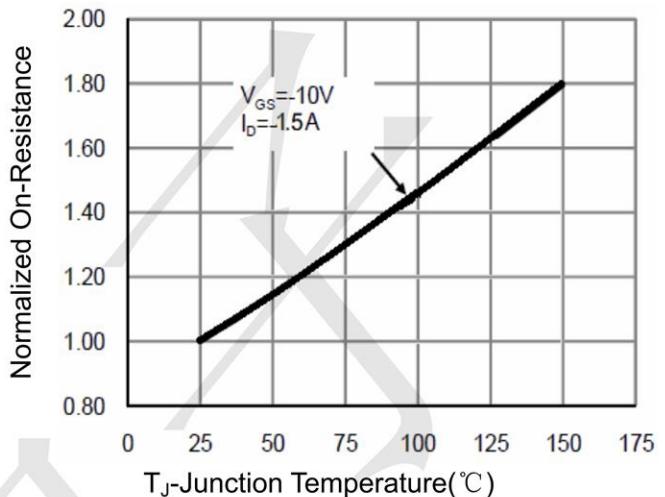
**Electrical Characteristics (  $T_A = 25^\circ\text{C}$  unless otherwise noted )**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-60	-	-	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=-60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	$\mu\text{A}$
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Gate-Body Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.4	-2.0	-2.6	V
Drain-Source On-State Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-1.5\text{A}$	-	150	200	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-1.5\text{A}$	-	190	240	$\text{m}\Omega$
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}}=-5\text{V}, I_{\text{D}}=-1.5\text{A}$	-	3	-	S
<b>Dynamic Characteristics</b> <small>(Note 4)</small>						
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=-30\text{V}, V_{\text{GS}}=0\text{V}, F=1.0\text{MHz}$	-	444.2	-	PF
Output Capacitance	$C_{\text{oss}}$		-	19.6	-	PF
Reverse Transfer Capacitance	$C_{\text{rss}}$		-	17.9	-	PF
<b>Switching Characteristics</b> <small>(Note 4)</small>						
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=-30\text{V}, I_{\text{D}}=-1.5\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{G}}=3\Omega$	-	40	-	nS
Turn-on Rise Time	$t_{\text{r}}$		-	35	-	nS
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	15	-	nS
Turn-Off Fall Time	$t_{\text{f}}$		-	10	-	nS
Total Gate Charge	$Q_{\text{g}}$	$V_{\text{DS}}=-30, I_{\text{D}}=-1.5\text{A}, V_{\text{GS}}=-10\text{V}$	-	11.3	-	nC
Gate-Source Charge	$Q_{\text{gs}}$		-	2.7	-	nC
Gate-Drain Charge	$Q_{\text{gd}}$		-	1.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <small>(Note 3)</small>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_{\text{S}}=-1.5\text{A}$	-		-1.2	V
Diode Forward Current <small>(Note 2)</small>	$I_{\text{S}}$		-	-	-1.6	A
Reverse Recovery Time	$t_{\text{rr}}$	$T_J = 25^\circ\text{C}, I_F = -1.5\text{A}$ $di/dt = -100\text{A}/\mu\text{s}$ <small>(Note 3)</small>	-	25		nS
Reverse Recovery Charge	$Q_{\text{rr}}$		-	31		nC

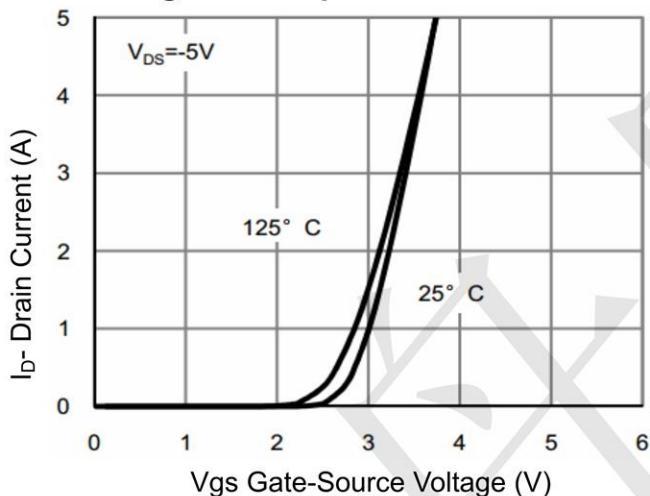
### Typical Electrical and Thermal Characteristics (Curves)



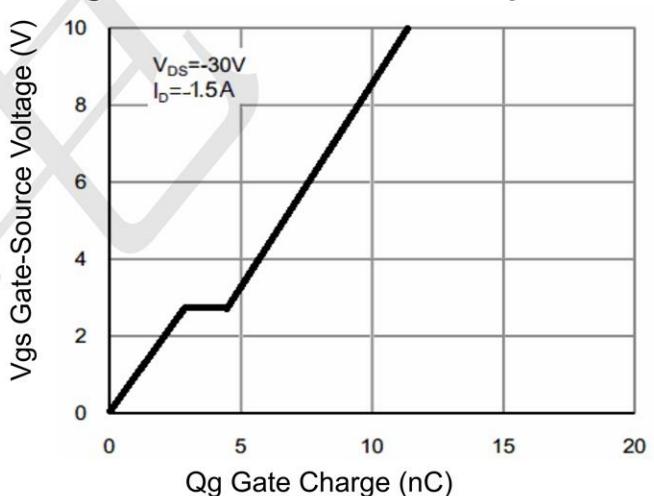
**Figure 1 Output Characteristics**



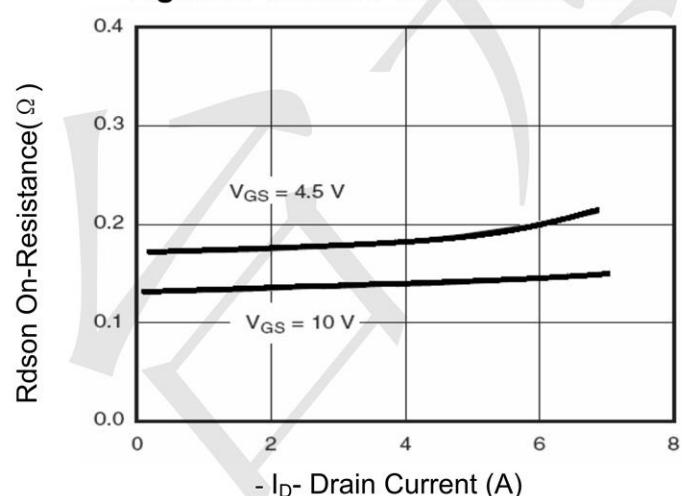
**Figure 4 Rdson-Junction Temperature**



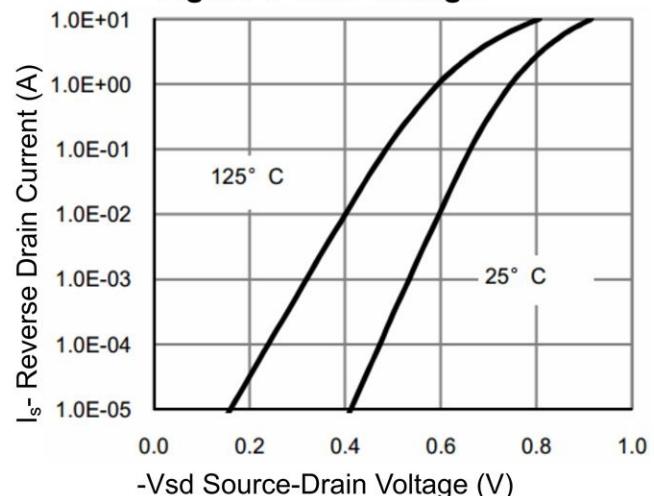
**Figure 2 Transfer Characteristics**



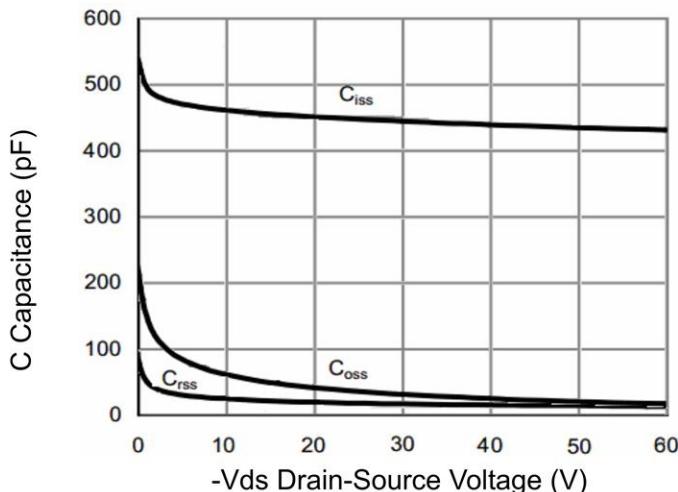
**Figure 5 Gate Charge**



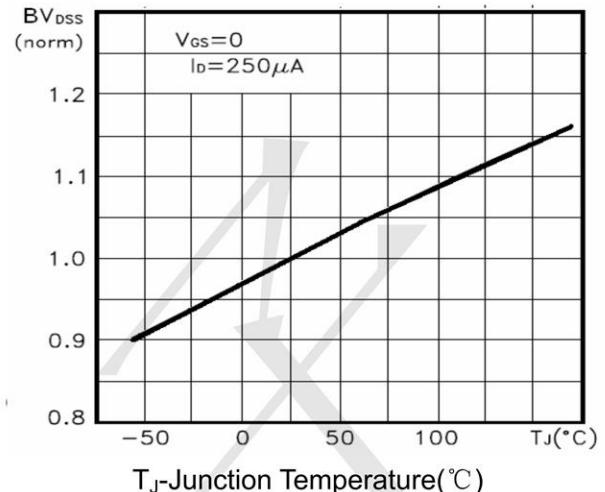
**Figure 3 Rdson- Drain Current**



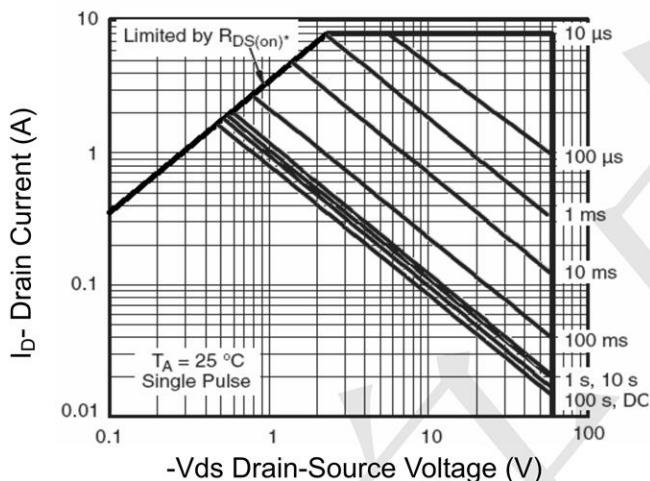
**Figure 6 Source- Drain Diode Forward**



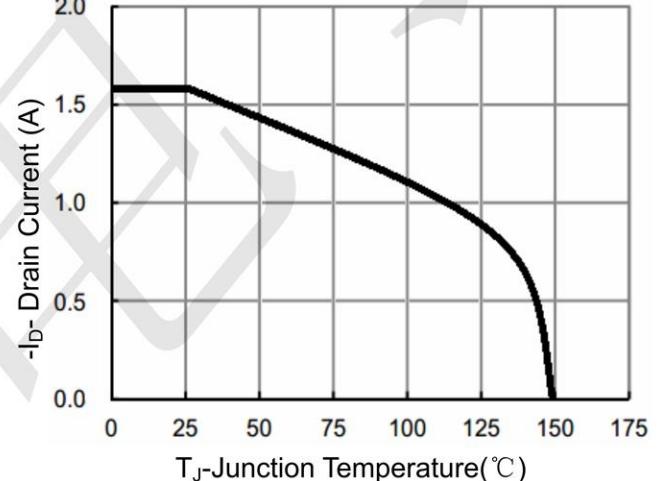
**Figure 7 Capacitance vs Vds**



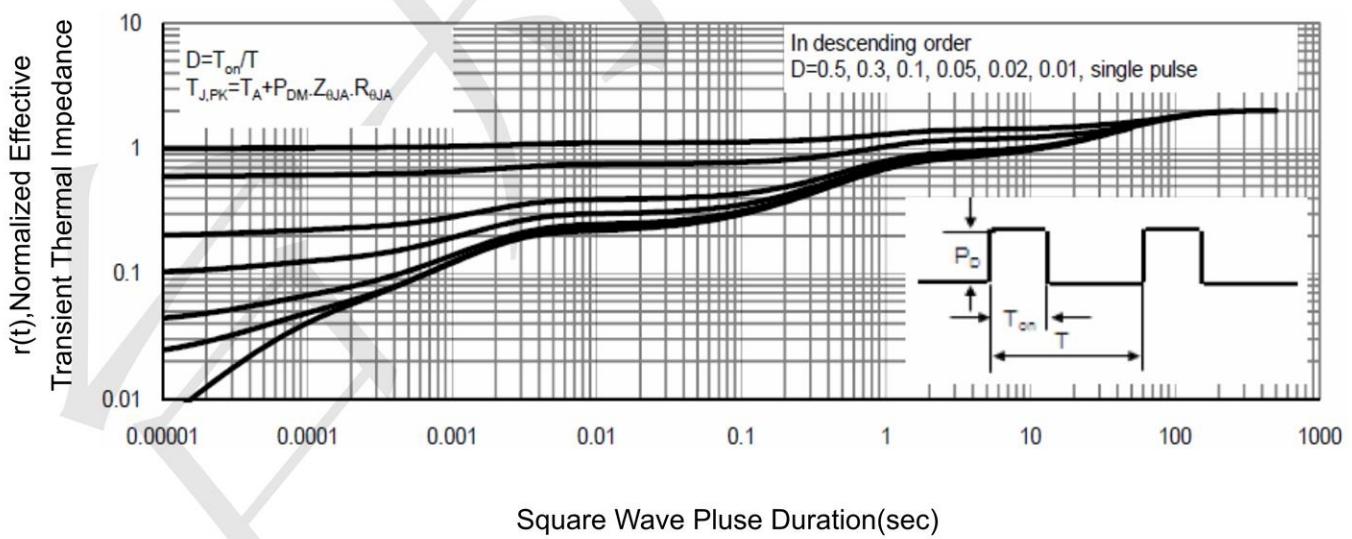
**Figure 9  $BV_{DSS}$  vs Junction Temperature**



**Figure 8 Safe Operation Area**

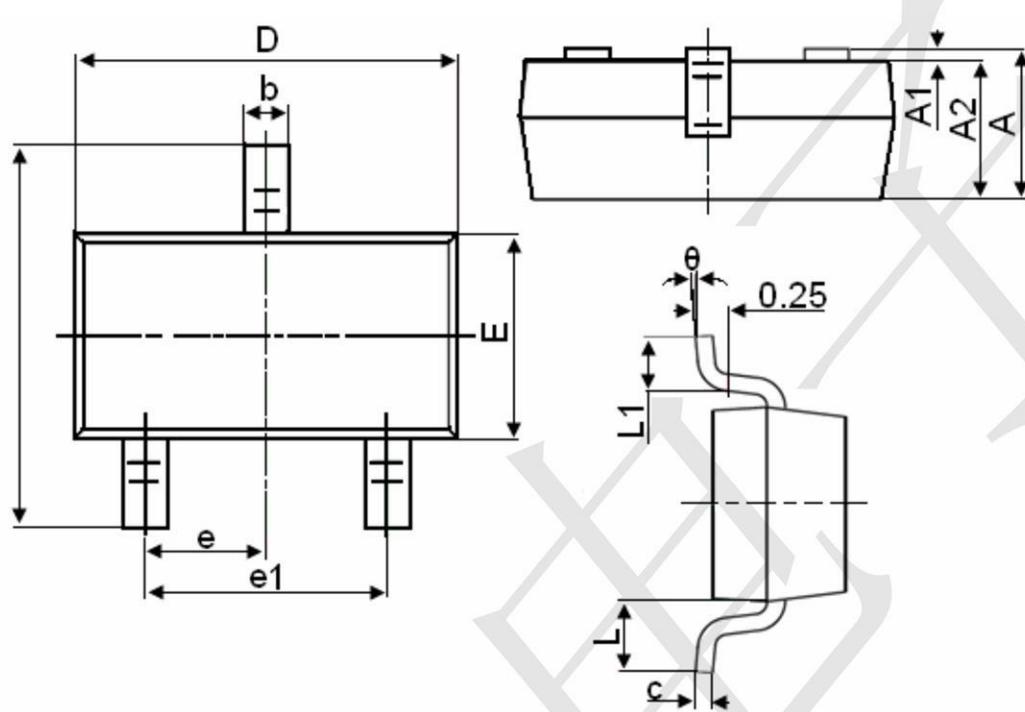


**Figure 10  $I_D$  Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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